

High Performance, 4-/8-Channel, Fault-Protected Analog Multiplexers

ADG438F/ADG439F

FEATURES

All switches off with power supply off
Analog output of on channel clamped within power supplies
if an overvoltage occurs
Latch-up proof construction
Fast switching times
ton 250 ns maximum
toff 150 ns maximum
Fault and overvoltage protection: -40 V to +55 V
Break-before-make construction

APPLICATIONS

Data acquisition systems
Industrial and process control systems
Avionics test equipment
Signal routing between systems
High reliability control systems

TTL- and CMOS-compatible inputs

GENERAL DESCRIPTION

The ADG438F and ADG439F are CMOS analog multiplexers, with the ADG438F comprising eight single channels and the ADG439F comprising four differential channels. These multiplexers provide fault protection. Using a series n-channel, p-channel, and n-channel MOSFET structure, both device and signal source protection is provided in the event of an overvoltage or power loss. The multiplexer can withstand continuous overvoltage inputs from –40 V to +55 V. During fault conditions with power supplies off, the multiplexer input (or output) appears as an open circuit and only a few nanoamperes of leakage current flows. This protects not only the multiplexer and the circuitry driven by the multiplexer, but also protects the sensors or signal sources which drive the multiplexer.

The ADG438F switches one of eight inputs to a common output as determined by the 3-bit binary address lines, A0, A1, and A2. The ADG439F switches one of four differential inputs to a common differential output as determined by the 2-bit binary address lines, A0 and A1. An EN input on each device is used to enable or disable the device. When disabled, all channels are switched off.

FUNCTIONAL BLOCK DIAGRAM

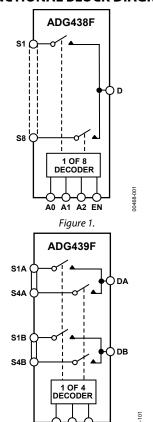


Figure 2.

PRODUCT HIGHLIGHTS

- Fault Protection. The ADG438F and ADG439F can withstand continuous voltage inputs up to −40 V or +55 V.
 When a fault occurs due to the power supplies being turned off, all the channels are turned off and only a leakage current of a few nanoamperes flows.
- 2. On channel saturates while fault exists.
- 3. Low Ron.
- 4. Fast Switching Times.
- 5. Break-Before-Make Switching. Switches are guaranteed break-before-make so that input signals are protected against momentary shorting.
- 6. Trench Isolation Eliminates Latch-Up. A dielectric trench separates the p-channel and n-channel MOSFETs thereby preventing latch-up.
- Improved Off Isolation. Trench isolation enhances the channel-to-channel isolation of the ADG438F/ADG439F.

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REVISION HISTORY

7/11—Rev. D to Rev. E

Updated FormatUniversa	ιI
Changes to Product Highlights Section and General	
Description	1
Changes to Specification Section and Table 1	3
Changes to Table 2	5
Added Table 3 and Table 4; Renumbered Sequentially	6
Changes to Figure 5 to Figure 10	7
Changes to Figure 11 to Figure 13	8
Added Figure 14 to Figure 16	8
Changes to Figure 18 to Figure 20, Figure 23, and Figure 24	9
Changes to Terminology Section1	2
Changes to Theory of Operation Section, Figure 29, and	
Figure 30 1	3
Updated Outline Dimensions1	4
Changes to Ordering Guide1	5

2/00—Rev. C to Rev. D

SPECIFICATIONS

DUAL SUPPLY

 V_{DD} = +15 V \pm 10%, V_{SS} = –15 V \pm 10%, GND = 0 V, unless otherwise noted.

Table 1.

B Version						
Parameter	+25°C	−40°C to +85°C	−40°C to +105°C	−40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH	+25 C	+63 C	+105 C	+125 C	Offic	rest conditions/comments
Analog Signal Range	V _{ss} + 1.4				V typ	Output open circuit
Allalog Signal Kange	$V_{DD} - 1.4$				V typ V typ	Output open circuit
	$V_{SS} - 1.4$ $V_{SS} + 2.2$				V typ V typ	Output loaded, 1 mA
	$V_{SS} + 2.2$ $V_{DD} - 2.2$				V typ V typ	Output loaded, I IIIA
Ron	270				Ωtyp	$-10 \text{ V} \le \text{V}_S \le +10 \text{ V}, \text{I}_S = 1 \text{ mA}$
NON	2/0	390	420	450	Ω max	See Figure 17
On-Resistance Flatness, RFLAT (ON)		390	420	450		
On-Resistance Flatness, R _{FLAT} (ON)	9	10	10	10	% typ	$-10 \text{ V} \le \text{V}_S \le +10 \text{ V}, \text{I}_S = 1 \text{ mA}$
D D.::4	10	10	10	10	% max	V 0VI 1 A
Ron Drift	0.6		_		%/°C typ	$V_S = 0 \text{ V}, I_S = 1 \text{ mA}$
On-Resistance Match Between	3	3	3	3	% max	$V_S = \pm 10 \text{ V, } I_S = 1 \text{ mA}$
Channels, Δ R _{ON}						
LEAKAGE CURRENTS	.0.65					
Source Off Leakage, Is (Off)	±0.01				nA typ	$V_D = \pm 10 \text{ V}, V_S = \mp 10 \text{ V}$
	±0.5	±1.5	±1.5	±4	nA max	See Figure 18
Drain Off Leakage, I _D (Off)	±0.01				nA typ	$V_D = \pm 10 \text{ V}, V_S = \mp 10 \text{ V}$
ADG438F ADG439F	±0.5	±5	±5	±20	nA max	See Figure 19
Channel On Leakage, I_D , I_S (On)	±0.01				nA typ	$V_S = V_D = \pm 10 \text{ V}$
ADG438F/ADG439F	±0.5	±5	±5	±20	nA max	See Figure 20
FAULT						
Source Leakage Current, Is (Fault)	±0.02				nA typ	$V_S = +55 \text{ V or } -40 \text{ V, } V_D = 0 \text{ V;}$ see Figure 21
(With Overvoltage)	±0.05	±0.1	±0.2	±0.2	μA max	
Drain Leakage Current, I _D (Fault)	±0.05				nA typ	$V_S = \pm 25 \text{ V}, V_D = \mp 10 \text{ V}$; see Figure 19
(With Overvoltage)	±0.05	±0.1	±0.2	±0.2	μA max	
Source Leakage Current, Is (Fault) (Power Supplies Off)	±30				nA typ	$V_S = \pm 25 \text{ V}, V_D = V_{EN}, A0, A1, A2 = 0 \text{ V}$
	±0.1	±0.2	±0.3	1	μA max	See Figure 22
DIGITAL INPUTS						
Input High Voltage, V _{INH}		2.4	2.4	2.4	V min	
Input Low Voltage, V _{INL}		0.8	0.8	0.8	V max	
Input Current						
I _{INL} or I _{INH}		±1	±1	±1	μA max	$V_{IN} = 0 \text{ V or } V_{DD}$
Digital Input Capacitance, C _{IN}	5				pF typ	
DYNAMIC CHARACTERISTICS ¹						
ttransition	175				ns typ	$R_L = 1 M\Omega$, $C_L = 35 pF$
	220	300	300	330	ns max	$V_{S1} = \pm 10 \text{ V}, V_{S8} = \mp 10 \text{ V}; \text{ see Figure 25}$
topen	90					
	60	40	40	40	ns min	$R_L = 1 \text{ k}\Omega$, $C_L = 35 \text{ pF}$, $V_S = 5 \text{ V}$; see Figure 26
ton (EN)	180				ns typ	$R_L = 1 \text{ k}\Omega$, $C_L = 35 \text{ pF}$
	230	300	300	345	ns max	$V_s = 5 \text{ V}$; see Figure 27
t _{OFF} (EN)	100				ns typ	$R_L = 1 \text{ k}\Omega, C_L = 35 \text{ pF}$
	130	150	150	173	ns max	$V_s = 5 \text{ V}$; see Figure 27

		B Ve	rsion			
Parameter	+25°C	−40°C to +85°C	−40°C to +105°C	−40°C to +125°C	Unit	Test Conditions/Comments
Settling Time, t _{SETT}						
0.1%		1	1	1	μs typ	$R_L = 1 \text{ k}\Omega, C_L = 35 \text{ pF}$
0.01%		2.5	2.5	2.5	μs typ	$V_S = 5 V$
Charge Injection	15				pC typ	$V_S = 0$ V, $R_S = 0$ Ω , $C_L = 1$ nF; see Figure 28
Off Isolation	93				dB typ	$R_L = 1 \text{ k}\Omega$, $C_L = 15 \text{ pF}$, $f = 100 \text{ kHz}$, $V_S = 7 \text{ V rms}$; see Figure 23
Channel-to-Channel Crosstalk	93				dB typ	$R_L = 1 \text{ k}\Omega$, $C_L = 15 \text{ pF}$, $f = 100 \text{ kHz}$, $V_S = 7 \text{ rms}$; see Figure 24
C _s (Off)	3				pF typ	
C _D (Off)						
ADG438F	22				pF typ	
ADG439F	12				pF typ	
POWER REQUIREMENTS						
I _{DD}	0.05				mA typ	$V_{IN} = 0 \text{ V or } 5 \text{ V}$
	0.1	0.2	0.2	0.2	mA max	
Iss	0.1				μA typ	
		1	1	1	μA max	

¹ Guaranteed by design, not subject to production test.

ABSOLUTE MAXIMUM RATINGS

 $T_A = 25$ °C unless otherwise noted.

Table 2.

ParameterRatingVDD to VSS48 VVDD to GND-0.3 V to +48 VVSS to GND+0.3 V to -48 VDigital Input, EN, Ax-0.3 V to VDD + 0.3 V or 20 mA, whichever occurs firstVS, Analog Input Overvoltage with Power On (VDD = +15 V, VSS = -15 V)VSS - 25 V to VDD + 40 VVS, Analog Input Overvoltage with Power Off (VDD = 0 V, VSS = 0 V)-40 V to +55 VContinuous Current, S or D20 mAPeak Current, S or D (Pulsed at 1 ms, 10% Duty Cycle Maximum)40 mAOperating Temperature Range Industrial (B Version)-40°C to +125°CStorage Temperature Range-65°C to +150°CJunction Temperature150°CPlastic DIP Package117°C/WΘJA, Thermal Impedance117°C/WSOIC Package0JA, Thermal ImpedanceNarrow Body125°C/WWide Body90°C/W	Table 2.	
V _{DD} to GND V _{SS} to GND Digital Input, EN, Ax V _S , Analog Input Overvoltage with Power On (V _{DD} = +15 V, V _{SS} = -15 V) V _S , Analog Input Overvoltage with Power Off (V _{DD} = 0 V, V _{SS} = 0 V) Continuous Current, S or D Peak Current, S or D (Pulsed at 1 ms, 10% Duty Cycle Maximum) Operating Temperature Range Industrial (B Version) Storage Temperature Range Junction Temperature Plastic DIP Package θ _{JA} , Thermal Impedance SOIC Package θ _{JA} , Thermal Impedance Narrow Body -0.3 V to +48 V +0.3 V to -48 V -0.3 V to -48 V -0.3 V to -48 V -0.3 V to +48 V +0.3 V to -48 V -0.3 V to -48 V -0.3 V to +48 V +0.3 V to -48 V -0.3 V to +48 V -0.3 V to -48 V -0.3 V to +48 V +0.3 V to -48 V -0.3 V to +48 V +0.3 V to -48 V -0.3 V to -48 V -0.3 V to +48 V -0.3 V to -48 V -0.3 V to -40 V -40 V to +55 V -40 V to +	Parameter	Rating
V _{SS} to GND Digital Input, EN, Ax V _S , Analog Input Overvoltage with Power On (V _{DD} = +15 V, V _{SS} = -15 V) V _S , Analog Input Overvoltage with Power Off (V _{DD} = 0 V, V _{SS} = 0 V) Continuous Current, S or D Peak Current, S or D (Pulsed at 1 ms, 10% Duty Cycle Maximum) Operating Temperature Range Industrial (B Version) Storage Temperature Range Junction Temperature Plastic DIP Package θ _{JA} , Thermal Impedance SOIC Package θ _{JA} , Thermal Impedance Narrow Body +0.3 V to -48 V -0.3 V to -48 V -0.3 V to -48 V -40 V to +55 V 20 mA 40 mA -40 °C to +125 °C -65 °C to +125 °C 150 °C	V _{DD} to V _{SS}	48 V
Digital Input, EN, Ax V _{Sr} , Analog Input Overvoltage with Power On (V _{DD} = +15 V, V _{SS} = -15 V) V _{Sr} , Analog Input Overvoltage with Power Off (V _{DD} = 0 V, V _{SS} = 0 V) Continuous Current, S or D Peak Current, S or D (Pulsed at 1 ms, 10% Duty Cycle Maximum) Operating Temperature Range Industrial (B Version) Storage Temperature Range Junction Temperature Plastic DIP Package θ _{JA} , Thermal Impedance SOIC Package θ _{JA} , Thermal Impedance Narrow Body -0.3 V to V _{DD} + 0.3 V or 20 mA, whichever occurs first V _{SS} - 25 V to V _{DD} + 40 V -40 V to +55 V 20 mA 40 mA -40 °C to +125 °C -65 °C to +150 °C 117 °C/W	V _{DD} to GND	−0.3 V to +48 V
whichever occurs first V_{SS} , Analog Input Overvoltage with Power On $(V_{DD} = +15 \text{ V}, V_{SS} = -15 \text{ V})$ Vs, Analog Input Overvoltage with Power Off $(V_{DD} = 0 \text{ V}, V_{SS} = 0 \text{ V})$ Continuous Current, S or D Peak Current, S or D (Pulsed at 1 ms, 10% Duty Cycle Maximum) Operating Temperature Range Industrial (B Version) Storage Temperature Range Junction Temperature Plastic DIP Package θ_{JA} , Thermal Impedance Narrow Body whichever occurs first $V_{SS} - 25 \text{ V}$ to $V_{DD} + 40 \text{ V}$ -40 V to $+55 \text{ V}$ -40 V to $+55 \text{ V}$ -40 mA $-40 mA$	V_{SS} to GND	+0.3 V to -48 V
Power On (V _{DD} = +15 V, V _{SS} = -15 V) V _S , Analog Input Overvoltage with Power Off (V _{DD} = 0 V, V _{SS} = 0 V) Continuous Current, S or D Peak Current, S or D (Pulsed at 1 ms, 10% Duty Cycle Maximum) Operating Temperature Range Industrial (B Version) Storage Temperature Range Junction Temperature Plastic DIP Package θ _{JA} , Thermal Impedance Narrow Body -40 °C to +125 °C -65 °C to +150 °C 117 °C/W	Digital Input, EN, Ax	•
Power Off (V _{DD} = 0 V, V _{SS} = 0 V) Continuous Current, S or D Peak Current, S or D (Pulsed at 1 ms, 10% Duty Cycle Maximum) Operating Temperature Range Industrial (B Version) Storage Temperature Range Junction Temperature Plastic DIP Package θ _{JA} , Thermal Impedance SOIC Package θ _{JA} , Thermal Impedance Narrow Body 20 mA 40 mA -40°C to +125°C -65°C to +150°C 150°C 117°C/W		$V_{SS} - 25 \text{ V to } V_{DD} + 40 \text{ V}$
Peak Current, S or D (Pulsed at 1 ms, 10% Duty Cycle Maximum) Operating Temperature Range Industrial (B Version) Storage Temperature Range Junction Temperature Plastic DIP Package θ _{JA} , Thermal Impedance SOIC Package θ _{JA} , Thermal Impedance Narrow Body 40 mA 40 mA 40 mA 40 mA 4125°C 150°C 150°C 117°C/W		-40 V to +55 V
10% Duty Cycle Maximum) Operating Temperature Range Industrial (B Version) Storage Temperature Range Junction Temperature Plastic DIP Package θ _{JA} , Thermal Impedance SOIC Package θ _{JA} , Thermal Impedance Narrow Body 125°C/W	Continuous Current, S or D	20 mA
Industrial (B Version) Storage Temperature Range Junction Temperature Plastic DIP Package θ _{JA} , Thermal Impedance SOIC Package θ _{JA} , Thermal Impedance Narrow Body -40°C to +125°C -65°C to +150°C 150°C 117°C/W 117°C/W		40 mA
Storage Temperature Range Junction Temperature Plastic DIP Package θ_{JA} , Thermal Impedance SOIC Package θ_{JA} , Thermal Impedance Narrow Body 125°C/W	Operating Temperature Range	
Junction Temperature Plastic DIP Package θ _{JA} , Thermal Impedance SOIC Package θ _{JA} , Thermal Impedance Narrow Body 150°C 117°C/W 125°C/W	Industrial (B Version)	-40°C to +125°C
Plastic DIP Package θ _{JA} , Thermal Impedance SOIC Package θ _{JA} , Thermal Impedance Narrow Body 125°C/W	Storage Temperature Range	−65°C to +150°C
 θ_{JA}, Thermal Impedance SOIC Package θ_{JA}, Thermal Impedance Narrow Body 117°C/W 125°C/W 	Junction Temperature	150°C
SOIC Package θ _{JA} , Thermal Impedance Narrow Body 125°C/W	Plastic DIP Package	
θ _{JA} , Thermal Impedance Narrow Body 125°C/W	θ_{JA} , Thermal Impedance	117°C/W
Narrow Body 125°C/W	SOIC Package	
	θ_{JA} , Thermal Impedance	
Wide Body 90°C/W	Narrow Body	125°C/W
	Wide Body	90°C/W

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

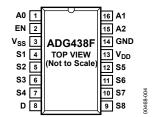


Figure 3. ADG438F Pin Configuration

A0 1		16 A1	
EN 2		15 GND	
V _{SS} 3	ADG439F	14 V _{DD}	
S1A 4	TOP VIEW	13 S1B	
S2A 5	(Not to Scale)	12 S2B	
S3A 6		11 S3B	
S4A 7		10 S4B	68-005
DA 8		9 DB	0468

Figure 4. ADG439F Pin Configuration

Table	Table 3. ADG438F Pin Function Description				
Pin					
No.	Mnemonic	Description			
1	A0	Logic Control Input.			
2	EN	Active High Digital Input. When low, the device is disabled, and all switches are off. When high, Ax logic inputs determine on switches.			
3	Vss	Most Negative Power Supply Potential. In single-supply applications, this pin can be connected to ground.			
4	S1	Source Terminal 1. This pin can be an input or an output.			
5	S2	Source Terminal 2. This pin can be an input or an output.			
6	S3	Source Terminal 3. This pin can be an input or an output.			
7	S4	Source Terminal 4. This pin can be an input or an output.			
8	D	Drain Terminal. This pin can be an input or an output.			
9	S8	Source Terminal 8. This pin can be an input or an output.			
10	S7	Source Terminal 7. This pin can be an input or an output.			
11	S6	Source Terminal 6. This pin can be an input or an output.			
12	S5	Source Terminal 5. This pin can be an input or an output.			
13	V_{DD}	Most Positive Power Supply Potential.			
14	GND	Ground (0 V) Reference.			
15	A2	Logic Control Input.			
16	A1	Logic Control Input.			

Table 5. ADG438F Truth Table¹

	Table 3.	MD 04301	. IIuuii I	ibic	
٠	A2	A1	A0	EN	On Switch
•	Χ	Χ	Χ	0	None
	0	0	0	1	1
	0	0	1	1	2
	0	1	0	1	3
	0	1	1	1	4
	1	0	0	1	5
	1	0	1	1	6
	1	1	0	1	7
	1	1	1	1	8

Table 4 ADC420E Din Expedien Description

Table	Table 4. ADG439F Pin Function Description				
Pin No.	Mnemonic	Description			
1	A0	Logic Control Input.			
2	EN	Active High Digital Input. When low, the device is disabled, and all switches are off. When high, Ax logic inputs determine on switches.			
3	V _{SS}	Most Negative Power Supply Potential. In single-supply applications, this pin can be connected to ground.			
4	S1A	Source Terminal 1A. This pin can be an input or an output.			
5	S2A	Source Terminal 2A. This pin can be an input or an output.			
6	S3A	Source Terminal 3A. This pin can be an input or an output.			
7	S4A	Source Terminal 4A. This pin can be an input or an output.			
8	DA	Drain Terminal A. This pin can be an input or an output.			
9	DB	Drain Terminal B. This pin can be an input or an output.			
10	S4B	Source Terminal 4B. This pin can be an input or an output.			
11	S3B	Source Terminal 3B. This pin can be an input or an output.			
12	S2B	Source Terminal 2B. This pin can be an input or an output.			
13	S1B	Source Terminal 1B. This pin can be an input or an output.			
14	V_{DD}	Most Positive Power Supply Potential.			
15	GND	Ground (0 V) Reference.			
16	A1	Logic Control Input.			

Table 6. ADG439F Truth Table¹

A1	A0	EN	On Switch Pair	
Χ	Х	0	None	
0	0	1	1	
0	1	1	2	
1	0	1	3	
1	1	1	4	

¹ X = don't care.

 $^{^{1}}$ X = don't care.

TYPICAL PERFORMANCE CHARACTERISTICS

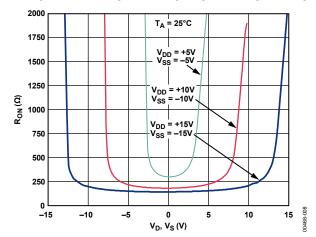


Figure 5. On Resistance as a Function of V_D (V_S)

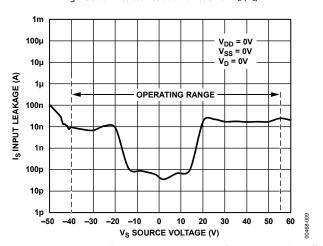


Figure 6. Source Input Leakage Current as a Function of V_s (Power Supplies Off) During Overvoltage Conditions

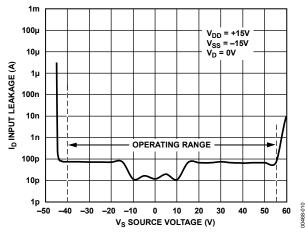


Figure 7. Drain Output Leakage Current as a Function of V_s (Power Supplies On)
During Overvoltage Conditions

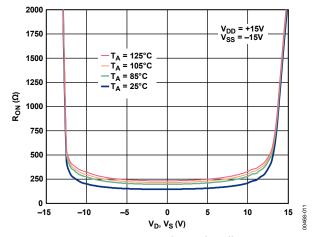


Figure 8. On Resistance as a Function of V_D (V_S) for Different Temperatures

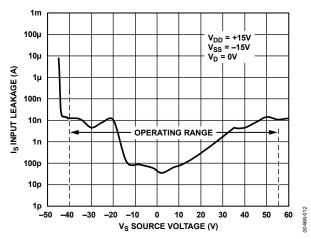


Figure 9. Source Input Leakage Current as a Function of V_s (Power Supplies On)

During Overvoltage Conditions

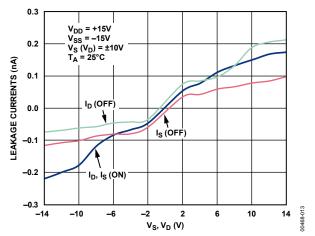


Figure 10. Leakage Currents as a Function of V_D (V_S)

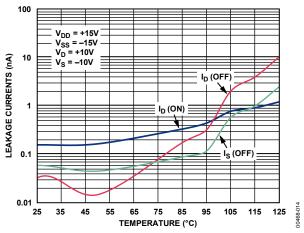


Figure 11. Leakage Currents as a Function of Temperature

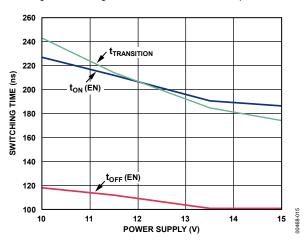


Figure 12. Switching Time vs. Dual Power Supply

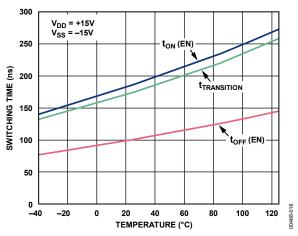


Figure 13. Switching Time vs. Temperature

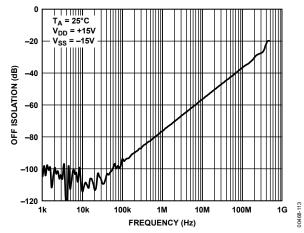


Figure 14. Off Isolation vs. Frequency, ±15 V Dual Supply

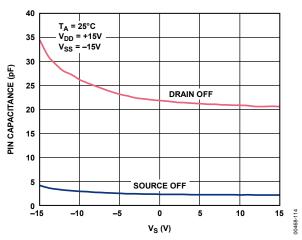


Figure 15. Capacitance vs. Source Voltage

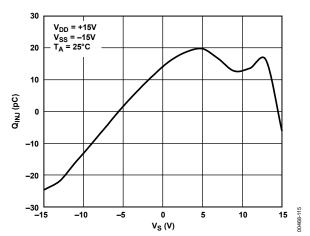


Figure 16. Charge Injection vs. Source Voltage

TEST CIRCUITS

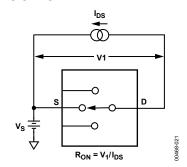


Figure 17. On Resistance

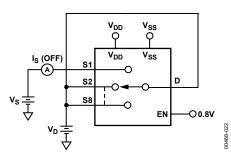


Figure 18. Is (Off)

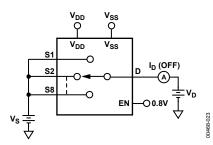
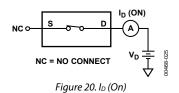


Figure 19. I_D (Off)



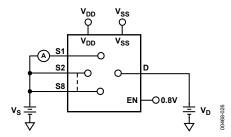


Figure 21. Input Leakage Current (with Overvoltage)

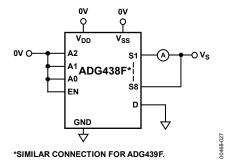


Figure 22. Input Leakage Current (with Power Supplies Off)

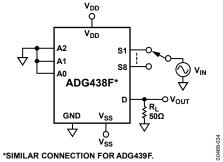


Figure 23. Off Isolation

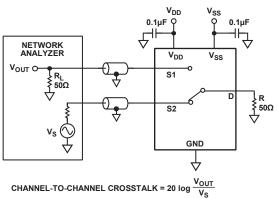


Figure 24. Channel-to-Channel Crosstalk

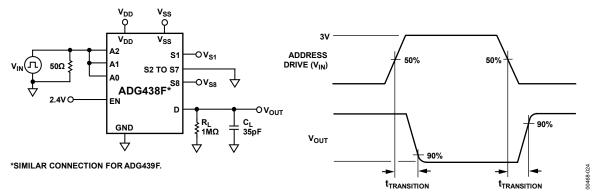


Figure 25. Switching Time of Multiplexer, ttransition

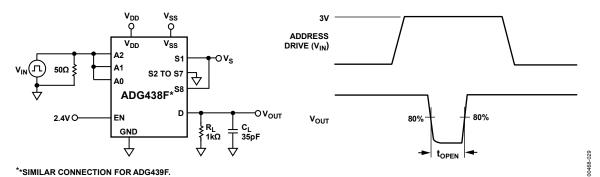


Figure 26. Break-Before-Make Delay, topen

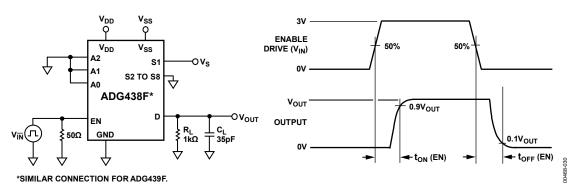


Figure 27. Enable Delay, ton (EN), toff (EN)

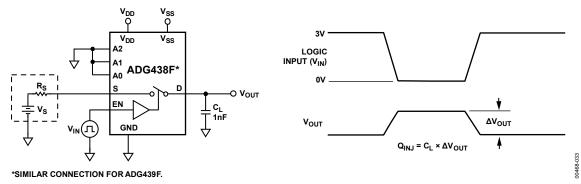


Figure 28. Charge Injection

TERMINOLOGY

 V_{DD}

Most positive power supply potential.

Vss

Most negative power supply potential.

GND

Ground (0 V) reference.

 \mathbf{R}_{ON}

Ohmic resistance between D and S.

 ΔR_{ON}

 $\Delta R_{\rm ON}$ represents the difference between the $R_{\rm ON}$ of any two channels as a percentage of the maximum $R_{\rm ON}$ of those two channels.

R_{FLAT (ON)}

Flatness is defined as the difference between the maximum and minimum value of the on resistance measured over the specified analog signal range and is represented by R_{FLAT (ON)}.

Flatness is calculated by

$$((R_{MAX}-R_{MIN})/R_{MAX}\times 100)$$

Ron Drift

Change in Ron when temperature changes by one degree Celsius.

Is (Off)

Source leakage current when the switch is off.

In (Off)

Drain leakage current when the switch is off.

 I_D , I_S (On)

Channel leakage current when the switch is on.

 $V_D (V_S)$

Analog voltage on Terminal D and Terminal S.

I_S (Fault—Power Supplies On)

Source leakage current when exposed to an overvoltage condition.

I_D (Fault—Power Supplies On)

Drain leakage current when exposed to an overvoltage condition.

Is (Fault—Power Supplies Off)

Source leakage current with power supplies off.

Cs (Off)

Channel input capacitance for off condition.

C_D (Off)

Channel output capacitance for off condition.

 C_D , C_S (On)

On switch capacitance.

CIN

Digital input capacitance.

ton (EN)

Delay time between the 50% and 90% points of the digital input and switch on condition.

toff (EN)

Delay time between the 50% and 90% points of the digital input and switch off condition.

tTRANSITION

Delay time between the 50% and 90% points of the digital inputs and the switch on condition when switching from one address state to another.

topen

Off time measured between 80% points of both switches when switching from one address state to another.

 V_{INL}

Maximum input voltage for Logic 0.

 V_{INH}

Minimum input voltage for Logic 1.

I_{INL} (I_{INH})

Input current of the digital input.

Off Isolation

A measure of unwanted signal coupling through an off channel.

Charge Injection

A measure of the glitch impulse transferred from the digital input to the analog output during switching.

 I_{DD}

Positive supply current.

Iss

Negative supply current.

THEORY OF OPERATION

The ADG438F/ADG439F multiplexers are capable of withstanding overvoltages from -40~V to +55~V, irrespective of whether the power supplies are present or not. Each channel of the multiplexer consists of an n-channel MOSFET, a p-channel MOSFET, and an n-channel MOSFET, connected in series. When the analog input exceeds the power supplies, one of the MOSFETs saturates, limiting the current. The current during a fault condition is determined by the load on the output. Figure 31 illustrates the channel architecture that enables these multiplexers to withstand continuous overvoltages.

When an analog input of $V_{\text{SS}}+2.2~V$ to $V_{\text{DD}}-2.2~V$ (output loaded, 1 mA) is applied to the ADG438F/ADG439F, the multiplexer behaves as a standard multiplexer, with specifications similar to a standard multiplexer, for example, the on-resistance is 270 Ω typically. However, when an overvoltage is applied to the device, one of the three MOSFETs saturates.

Figure 29 to Figure 32 show the conditions of the three MOSFETs for the various overvoltage situations. When the analog input applied to an on channel approaches the positive power supply line, the n-channel MOSFET saturates because the voltage on the analog input exceeds the difference between $V_{\rm DD}$ and the n-channel threshold voltage ($V_{\rm TN}$). When a voltage more negative than $V_{\rm SS}$ is applied to the multiplexer, the p-channel MOSFET saturates because the analog input is more negative than the difference between $V_{\rm SS}$ and the p-channel threshold voltage ($V_{\rm TP}$). Because $V_{\rm TN}$ is nominally 1.4 V and $V_{\rm TP}-1.4$ V, the analog input range to the multiplexer is limited to $V_{\rm SS}+1.4$ V to $V_{\rm DD}-1.4$ V (output open circuit) when a ± 15 V power supply is used.

When the power supplies are present but the channel is off, again either the p-channel MOSFET or one of the n-channel MOSFETs remains off when an overvoltage occurs.

Finally, when the power supplies are off, the gate of each MOSFET is at ground. A negative overvoltage switches on the first n-channel MOSFET, but the bias produced by the overvoltage causes the p-channel MOSFET to remain turned off. With a positive overvoltage, the first MOSFET in the series remains off because the gate to source voltage applied to this MOSFET is negative.

During fault conditions (power supplies off), the leakage current into and out of the ADG438F/ADG439F is limited to a few microamps. This limit protects the multiplexer and succeeding circuitry from over stresses as well as protects the signal sources that drive the multiplexer. Also, the other channels of the multiplexer are undisturbed by the overvoltage and continue to operate normally.

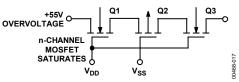


Figure 29. +55 V Overvoltage Input to the On Channel

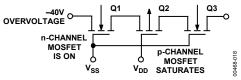


Figure 30. –40 V Overvoltage on an Off Channel with Multiplexer Power On

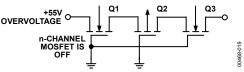


Figure 31. +55 V Overvoltage with Power Off

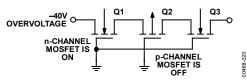
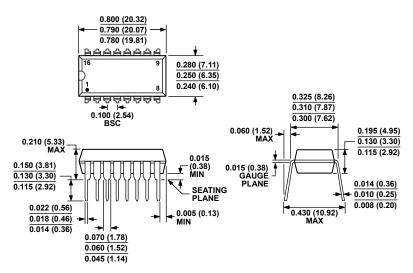


Figure 32. -40 V Overvoltage with Power Off

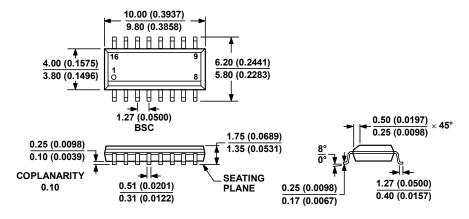
OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MS-001-AB

CONTROLLING DIMENSIONS ARE IN INCHES; MILLIMETER DIMENSIONS (IN PARENTHESES) ARE ROUNDED-OFF INCH EQUIVALENTS FOR REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN. CORNER LEADS MAY BE CONFIGURED AS WHOLE OR HALF LEADS.

Figure 33. 16-Lead Plastic Dual In-Line Package [PDIP] Narrow Body (N-16) Dimensions shown in inches and (millimeters)

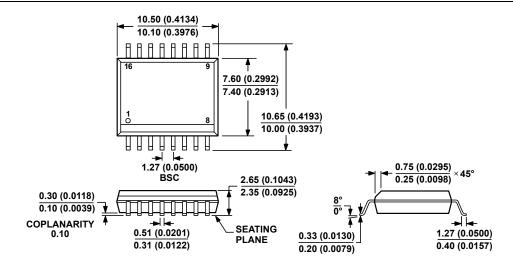


COMPLIANT TO JEDEC STANDARDS MS-012-AC

CONTROLLING DIMENSIONS ARE IN MILLIMETERS; INCH DIMENSIONS (IN PARENTHESES) ARE ROUNDED-OFF MILLIMETER EQUIVALENTS FOR REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

Figure 34. 16-Lead Standard Small Outline Package [SOIC_N] Narrow Body (R-16) Dimensions shown in millimeters and (inches) 906-A

03-27-2007-B



COMPLIANT TO JEDEC STANDARDS MS-013-AA
CONTROLLING DIMENSIONS ARE IN MILLIMETERS; INCH DIMENSIONS
(IN PARENTHESES) ARE ROUNDED-OFF MILLIMETER EQUIVALENTS FOR
REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

Figure 35. 16-Lead Standard Small Outline Package [SOIC_W]
Wide Body
(RW-16)
Dimensions shown in millimeters and (inches)

ORDERING GUIDE

Model ¹	Temperature Range	Package Description	Package Option
ADG438FBN	-40°C to +125°C	16-Lead Plastic Dual In-Line Package [PDIP]	N-16
ADG438FBNZ	-40°C to +125°C	16-Lead Plastic Dual In-Line Package [PDIP]	N-16
ADG438FBR	-40°C to +125°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG438FBR-REEL	-40°C to +125°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG438FBRZ	-40°C to +125°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG438FBRZ-REEL	-40°C to +125°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG439FBN	-40°C to +125°C	16-Lead Plastic Dual In-Line Package [PDIP]	N-16
ADG439FBNZ	-40°C to +125°C	16-Lead Plastic Dual In-Line Package [PDIP]	N-16
ADG439FBR	-40°C to +125°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG439FBR-REEL	-40°C to +125°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG439FBRW	-40°C to +125°C	16-Lead Standard Small Outline Package [SOIC_W]	RW-16
ADG439FBRWZ	-40°C to +125°C	16-Lead Standard Small Outline Package [SOIC_W]	RW-16
ADG439FBRWZ-REEL	-40°C to +125°C	16-Lead Standard Small Outline Package [SOIC_W]	RW-16
ADG439FBRZ	-40°C to +125°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG439FBRZ-REEL	-40°C to +125°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16

 $^{^{1}}$ Z = RoHS Compliant Part.

ADG438F/ADG439F	
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NOTES

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Analog Devices Inc.:

ADG438FBRZ ADG438FBRZ-REEL